Transfer Characteristics of $\text{H}_2\text{O}_2$-Doped ZrInZnO Thin Film Transistors

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Solution-processed zirconium-Indium-zinc-oxide thin-film transistors (ZIZO TFTs) were fabricated with and without hydrogen peroxide ($\text{H}_2\text{O}_2$). With an incorporation of $\text{H}_2\text{O}_2$ into the channel layer, threshold voltage shift under positive bias stress were improved. We realized the reduced trap density of ZIZO TFTs with 2 M $\text{H}_2\text{O}_2$ incorporation.